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GATE 2019 Electronics Engineering

Memory Based Questions and Solutions

Date of Exam: 9/2/2019

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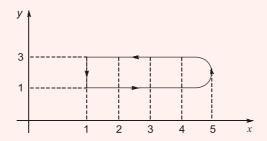
Q.1 The correct relation between the responsivity (R), quantum efficiency (η) and wavelength in micrometers (λ) is

Sol.

$$R = \frac{n\lambda}{1.24}$$

End of Solution

The value of $\int xdy - ydx$ is ___. Where *c* is shown below. Q.2

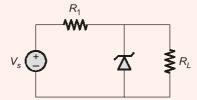


Sol.

$$\int_{C} xdy - ydx = \int_{\langle R \rangle} 2dxdy = 2(\text{area under curve})$$

$$= 2 \left[(2 \times 3) + \frac{1}{2} \pi (1)^2 \right] = 12 + \pi$$

 $R_{\rm 1}$ = 200 Ω , $R_{\rm L}$ = 1 k Ω , $V_{\rm Z}$ = 20 V and $I_{\rm Z(max)}$ = 60 mA. Find the range of $V_{\rm S}$ for which Q.3 Zener diode operates in reverse breakdown region?



Sol.

$$V_{s(\text{min})} = 20 \text{ V} + \left(\frac{20 \text{ V}}{1 \text{ k}\Omega} \times 200 \Omega\right) = 24 \text{ V}$$

 $V_{s(\text{max})} = 20 \text{ V} + \left(\frac{20 \text{ V}}{1 \text{ k}\Omega} + 60 \Omega\right) (200 \Omega) = 36 \text{ V}$

End of Solution

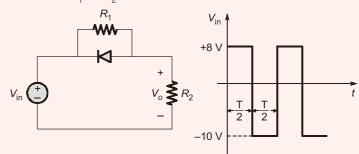
- The value of $\frac{1}{2\pi i} \oint_{C} \left(z + \frac{1}{z}\right)^{2} dz$ is _____. Where c is the unit circle in z-plane. Q.4
- (0)Sol.
- Q.5 The number of distinct eigen values are possible for the following matrix is _____.

$$A = \begin{bmatrix} 2 & 2 & 3 & 4 \\ 0 & 3 & 5 & 6 \\ 0 & 0 & 1 & 7 \\ 0 & 0 & 0 & 2 \end{bmatrix}$$

- Sol. Eigen values = Diagonal values = 2, 3, 1, 2 Number of distinct eigen values = 3
- End of Solution

End of Solution

Q.6 Diode is ideal and $R_1 = R_2 = 500 \ \Omega$.

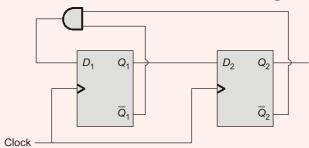


Average value of output voltage is _____ V.

Sol.
$$V_{o \text{ (avg)}} = \frac{4-10}{2} = -3 \text{ V}$$

End of Solution

Q.7 Input clock frequency is 12 kHz. Find the frequency of Q_2 ?



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Sol.

PS		D_2	D_1	NS		
Q ₂	Q ₁	\setminus	<	Q ₂ ⁺	Q_1^{\dagger}	
0	0	0	1	0	1	•
0	1	1	0	1	0	
1	0	0	0	0	0	

$$D_1 = \overline{Q}_2 \overline{Q}_1 = \overline{Q_2 + Q_1}$$

$$\mathsf{MOD} \, = \, 3$$

$$MOD = 3$$

$$f_{Q2} = \frac{f_{\text{olk}}}{3} = \frac{12}{3} \text{ kHz} = 4 \text{ kHz}$$

Q.8 Two wires W_1 and W_2 are separated by a distance of "4r" and carrying current I and 21 respectively in opposite direction. The magnitude of magnetic flux density at a distance of "r" from W_1 is _____

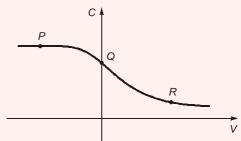
Sol.

$$H_1 = \frac{I}{2\pi r}$$
; $H_2 = \frac{2I}{2\pi (3r)}$

$$B = \mu_0(H_1 + H_2) = \frac{I\mu_0}{2\pi r} \left(1 + \frac{2}{3} \right) = \frac{5I\mu_0}{6\pi r}$$

End of Solution

The high frequency C-V plot of an n-channel MOSFET is given below: Q.9



The flat band, inversion and accumulation situations are depicted by respectively

(a) P, Q, R

(b) Q, R, P

(c) R, Q, P

(d) Q, P, R

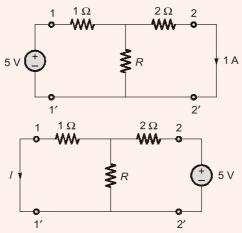
Sol. (b)



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Q.10 Consider the figures shown in the circuit below.

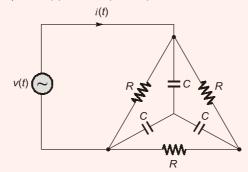


Find the value of current I?

According to reciprocity theorem, Sol.

$$I = 1 A$$

 $R = 1 \text{ k}\Omega$; $C = 1 \text{ }\mu\text{F}$; $v(t) = 3\sin(1000t) \text{ V}$. Q.11



Find the steady state current i(t).

End of Solution

End of Solution

X and Y are two random variables and Q.12

$$E[2X + Y] = 0$$

 $E[X + 2Y] = 33$

The value E[X + Y] is _____.

Sol.
$$E[2X + Y] = 2\overline{X} + \overline{Y} = 0$$
 ...(i)

$$E[X + 2Y] = \overline{X} + 2\overline{Y} = 33$$
 ...(ii)

Adding equations (i) and (ii)

$$3\overline{X} + 3\overline{Y} = 33 \implies \overline{X} + \overline{Y} = 11$$

 $E[X + Y] = \overline{X} + \overline{Y} = 11$ So,

Q.13 Match the below two lists:

- **1**. ∇. \vec{D}
- 2. $\nabla \times \vec{E}$
- **3**. ∇. \vec{R}
- 4. $\nabla \times \vec{H}$

- **P.** 0
- **Q**. ρ
- $\mathbf{R.} \quad -\frac{\partial \vec{B}}{\partial t}$
- S. $\sigma \vec{E} + \frac{\partial \vec{D}}{\partial t}$

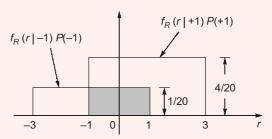
Sol.

- 1. $\nabla \cdot \vec{D} = \rho$
- $2. \quad \nabla \times \vec{E} = -\frac{\partial \vec{B}}{\partial t}$
- $\mathbf{3.} \quad \nabla \cdot \vec{B} = 0$
- **4**. $\nabla \times \vec{H} = \sigma \vec{E} + \frac{\partial \vec{D}}{\partial t}$

End of Solution

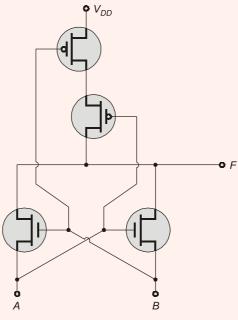
Q.14 X is a random variable, which takes the values -1 and +1 with probabilities 0.2 and 0.8 respectively. It is passed through a noisy channel such that the received signal at the output is X + N, where N is independent of X and uniformly distributed over [-2, 2]. If optimum threshold is selected to minimise the probability of error, then the minimum error probability will be _

Sol.



Ans = Shaded area =
$$2 \times \frac{1}{20} = 0.10$$

Q.15 The following circuit works as



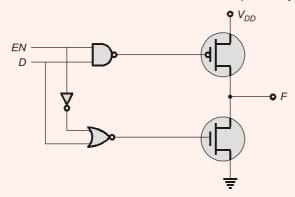
- (a) XNOR
- (c) XOR

- (b) Latch
- (d) SRAM cell

Sol. (a)

= ● ● ● End of Salution

Q.16 When EN = 0 and EN = 1, the state of F will be respectively.



 $EN = 0 \Rightarrow \text{High-Z}$ $EN = 1 \Rightarrow F = D$ It acts as a tristate buffer Sol.

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A message signal, having frequencies in the range 5 to 15 kHz, is amplitude modulated Q.17 with a carrier frequency of 600 kHz. The resultant signal is sampled with 1.2 times the Nyquist rate and quantized using a 256-level quantizer. The final data rate will be ____ Mbps.

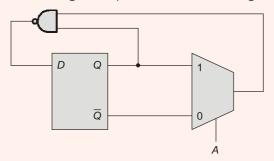
Sol.

$$f_{\rm max} = 600 + 15 = 615 \text{ kHz}$$

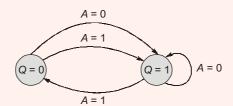
 $f_{\rm s} = 1.2 \times 2 \times 615 = 1476 \text{ kHz}$
 $R_{\rm b} = 8f_{\rm s} = 11808 \text{ kbps} = 11.808 \text{ Mbps}$

● ● End of Solution

Select the correct state diagram representation of this logic circuit. Q.18

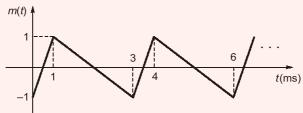


Sol.



End of Solution

Q.19 The following message signal is applied to a phase modulator with $K_p = 10\pi$.



If $f_c = 50$ kHz and maximum instantaneous frequency of the modulated signal is $f_{\rm max}$ and minimum instantaneous frequency is f_{\min} , then the ratio of f_{\max} to f_{\min} is _____.

Sol.

$$\frac{f_{\text{max}}}{f_{\text{min}}} = \frac{60}{45} = 1.33$$

An exponential random variable is given, such that its cumulative distribution function Q.20 (CDF) is given by,

$$F_{Z}(x) = \begin{cases} (1 - e^{-x}); & x \ge 0\\ 0; & \text{otherwise} \end{cases}$$

Find the probability $P\{z>2|z>1\}$.

Required probability = $\frac{P[(z>2) \cap (z>1)]}{P[z>1]} = \frac{P[z>2]}{P[z>1]}$ Sol.

$$P(z \le 2) = 1 - e^{-2} \Rightarrow P(z > 2) = e^{-2}$$

 $P(z \le 1) = 1 - e^{-1} \Rightarrow P(z > 1) = e^{-1}$

So, Required probability = $\frac{e^{-2}}{c^{-1}} = e^{-1} \simeq 0.37$

End of Solution

An infinite line carrying a charge density of Q. The value of $\int \vec{E} \cdot \vec{da}$ over the surface Q.21 formed by a quarter cylinder of height H and radius R.

Sol.

$$2\pi RHD = QH$$

$$D = \frac{Q}{2\pi R}$$

$$E = \frac{Q}{2\pi \epsilon_o R}$$

$$\int \vec{E} \cdot \vec{da} = \int \int ERd\phi dz = \frac{Q}{2\pi \epsilon_o} \times \frac{\pi}{2} \times H = \frac{QH}{4\epsilon_o}$$

End of Solution

Q.22 The value of $\int_{0}^{\pi} \int_{x}^{\pi} \frac{\sin(x)}{x} dx dy$ is _____.

End of Solution

Q.23 $\frac{dy}{dx} = -\left(\frac{x}{v}\right)^n$

For n = -1 and n + 1, the solution of the above given differential equation respectively represent

- (a) parabola and circle
- (b) hyperbola and circle
- (c) hyperbola and parabola
- (d) circle and hyperbola

● ● End of Solution



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- One machine can complete a work in 4 hours, another machine can complete the same work Q.24 in 2 hours. If both the machines work together, the same work can be completed in
 - (a) 1 hour

(b) 3 hours

(c) 4/3 hours

(d) 2 hours

End of Solution

End of Solution

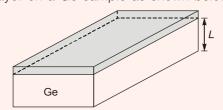
- Q.25 When he did not come to home, she _____ him died at roadside somewhere.
 - (a) noticed

(b) looked

(c) pictured

(d) concluded

Q.26 Consider the SiO₂ layer on a Ge sample as shown below.



A Laser light, with a wavelength of 600 nm is falling on the surface of SiO₂ layer. Half of the incident power is reflected by the SiO2 surface and remaining half reached the interface of SiO₂-Ge. One third of the remaining power is reflected by the SiO₂-Ge interface, one third is absorbed by Ge sample and remaining one third comes out from the sample. The absorption coefficient of the Ge is 3×10^4 cm⁻¹. The thickness of the Ge sample is _____ µm.

Sol.

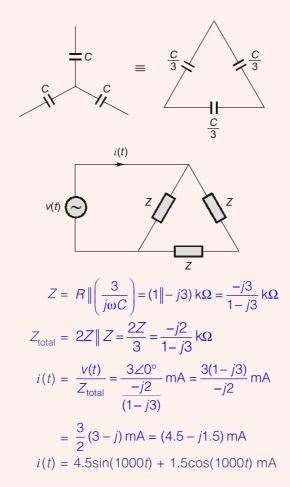
$$\frac{2}{3}e^{-\alpha L} = \frac{1}{3}$$

$$\alpha = 3 \times 10^{4} \text{ cm}^{-1}$$

$$L = \frac{1}{\alpha}\ln(2) \text{ cm} = \frac{0.693}{3} \text{ } \mu\text{m} = 0.231 \mu\text{m}$$

A rectangular waveguide with dimension width (w) and height (h has cut-off frequency Q.27 of TE_{10} and TM_{11} mode with a ratio of 1:2. The aspect ratio (w/h) of the waveguide

Sol.



Q.28 A block diagram has been given in the question, whose close-loop transfer function will be.

$$T(s) = \frac{K}{s^3 + 3s^2 + 2s + K}$$

The value of K for which two of its poles lie on the imaginary axis in s-plane is $\underline{}$.

 $K_{\text{mar}} = 2 \times 3 = 6$ Sol.



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Q.29 For a diode with $\eta = 1$, the magnitude of reverse biased voltage needed to reach 75% of its reverse saturation current is _____ mV.

Sol.

$$I_o (e^{V_{BE}/V_T} - 1) = -\frac{3}{4} I_o$$
 (Take $V_T = 25.9 \text{ mV}$)

On solving,

$$V_{RF} = -35.9 \text{ mV}$$

$$\Rightarrow$$

$$V_{\rm p} = |V_{\rm BF}| = 35.9 \,\rm mV$$

The transfer function of a system is, Q.30

$$\frac{Y(s)}{U(s)} = \frac{1}{s^3 + 3s^2 + 2s + 1}$$

Its state space representation is,

$$\dot{x} = Ax + Bu$$

$$y = Cx$$

If $B = [0 \ 0 \ 1]^T$, then the correct representation of matrices A and C is

Sol.

$$A = \begin{bmatrix} 0 & 1 & 0 \\ 0 & 0 & 1 \\ -1 & -2 & -3 \end{bmatrix}; C = \begin{bmatrix} 1 & 0 & 0 \end{bmatrix}$$

End of Solution

■ ● ■ End of Solution

